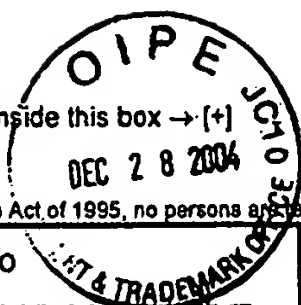


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				Application Number	09/535,015
				Filing Date	March 24, 2000
				First Named Inventor	Shunpei YAMAZAKI et al.
				Group Art Unit	2811
				Examiner Name	S. Crane
				Attorney Docket Number	0756-2131
Sheet	1	of	1		

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Examiner Signature	CRANE	Date Considered	5/2005
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Applicants: Shupei YAMAZAKI et al.

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Group Art Unit: 2825

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				Filing Date: March 24, 2000		Group Art Unit: 2825	
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Examiner Name	S. Crane
Attorney Docket Number	0756-2131

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known			
				Application Number		09/535,015	
				Filing Date		March 24, 2000	
				First Named Inventor		Shunpei YAMAZAKI et al.	
				Group Art Unit		2811	
				Examiner Name		S. Crane	
Sheet	2	of	2	Attorney Docket Number		0756-2131	

U.S. PATENT DOCUMENTS						
Examiner Initials	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
SWC		6,162,704		Yamazaki et al.	12/19/2000	
		6,294,441		Yamazaki	09/25/2001	
		6,461,943		Yamazaki et al.	10/08/2002	
SWC		6,620,711		Yamazaki	09/16/2003	

FOREIGN PATENT DOCUMENTS								
Examiner Initials ²	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ³
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
SWC		JP	07-066425			03/10/1995		Abst. & U.S. Equiv.
		JP	08-045839			02/16/1996		Abst. & U.S. Equiv.
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		JP	08-097169			04/12/1996		Abst. & U.S. Equiv.
SWC		KR	96-005879			02/23/1996		U.S. Equiv.

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²

Examiner Signature	CRANE	Date Considered	5/2005
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Please type a plus sign (+) inside this box → (+)

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SWL		5,132,754		Serikawa et al.	07/21/1992	

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Examiner Signature	CRANE	Date Considered	5/2005
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